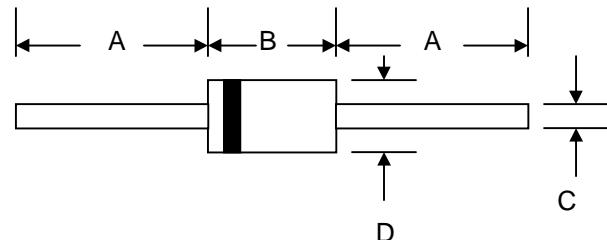




Features

- Low VF Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free:** For RoHS / Lead Free Version

DO-201AD		
Dim	Min	Max
A	24.5	—
B	7.20	9.50
C	1.10	1.30
D	5.00	5.60

All Dimensions in mm

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	SR530L	SR540L	SR545L	SR550L	SR560L	SR580L	SR5100L	SR5150L	SR5200L	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	40	45	50	60	80	100	150	200	V
RMS Reverse Voltage	V _{R(RMS)}	21	28	31.5	35	42	56	70	105	140	V
Average Rectified Output Current @T _L = 75°C (Note 1)	I _O										A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}										A
Forward Voltage @I _F = 5.0A	V _{FM}		0.45		0.5		0.6		0.85		V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}			0.2			0.1				mA
Typical Junction Capacitance (Note 2)	C _J		500				350				pF
Typical Thermal Resistance (Note 1)	R _{θJA}				25						°C/W
Operating and Storage Temperature Range	T _j , T _{STG}				-55 to +150						°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

